L Number	Hits	Search Text	DB	Time stamp
•	4	((xide-nitride r xynitride r xy-nitride) near2 gate near2 (insulator or insulating	USPAT; US-PGPUB;	2003/12/11 13:43
		dielectric)).clm. and (oxide near2 gate near2 (dielectric or insulating or	EPO; JPO; DERWENT;	
-	2780	insulator)).clm. ((ozone or ozonated or ozonating)) same	IBM_TDB USPAT;	2003/12/11
		oxide same film	US-PGPUB; EPO; JPO;	13:44
			DERWENT; IBM_TDB	
-	10573	((ozone or ozonated or ozonating)) same (oxide)	USPAT; US-PGPUB;	2003/12/11 13:44
			EPO; JPO; DERWENT;	
-	42	(oxide adj film).clm. and (ozone or ozonation).clm.	IBM_TDB USPAT;	2003/12/11
		and (silicon adj nitride adj film).clm.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	13:45
•	9	(oxide adj film).clm. same (ozone or	USPAT;	2003/12/11
		ozonating or ozonated or ozonation).clm. same(silicon adj nitride adj film).clm.	US-PGPUB; EPO; JPO; DERWENT;	13:45
-	9	(oxide adj film).clm. same (ozone or	IBM_TDB USPAT;	2003/12/11
		ozonating or ozonated or ozonation).clm. same (silicon adj nitride adj film).clm.	US-PGPUB; EPO; JPO; DERWENT;	13:46
-	0	(oxide adj (layer or film)).clm. same	IBM_TDB USPAT;	2003/12/11
		(ozonating or ozonated or ozonation).clm. same (silicon adj nitride adj (layer or film)).clm.	US-PGPUB; EPO; JPO; DERWENT;	13:47
-	0	(oxide adj (layer or film)).clm. same	IBM_TDB USPAT;	2003/12/11
		(ozonating or ozonated or ozonation).clm. same (((silicon adj nitride) or SiN) adj (layer or film)).clm.	US-PGPUB; EPO; JPO; DERWENT;	13:48
	o	(oxide adj (layer or film)).clm. and	IBM_TDB USPAT;	2003/12/11
		(ozonating or ozonated or ozonation).clm. and (((silicon adj nitride) or SiN) adj (layer r film)).clm.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	13:48
	0	(oxide adj (layer or film)) and (zonating or zonated or zonati n).clm. and (((silicon adj nitride) r SiN) adj (lay r or film))	USPAT; US-PGPUB; EPO; JPO;	2003/12/11 13:48
			DERWENT; IBM_TDB	

-	354	(oz nated or zonating or ozonation r	USPAT;	2003/12/11
		ozonate).clm.	US-PGPUB;	13:49
			EPO; JPO;	
			DERWENT;	}
			IBM_TDB	
-	6	((ozonated or ozonating or ozonation or	USPAT;	2003/12/11
		ozonate) near (substrate or substance or	US-PGPUB;	13:49
		element)).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	114	((ozonated or ozonating or ozonation or	USPAT;	2003/12/11
		ozonate)) near10 (film or layer)	US-PGPUB;	13:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	17	(((ozonated or ozonating or ozonation or	USPAT;	2003/12/11
		ozonate)) near10 (film or layer)).clm.	US-PGPUB;	13:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	(((ozonated or ozonating or ozonation or	USPAT;	2003/12/11
		ozonate)) near10 (film)).clm.	US-PGPUB;	13:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5	(((ozonated or ozonating or ozonation or	USPAT;	2003/12/11
		ozonate)) near10 (film or layer) near10	US-PGPUB;	13:52
		oxide).clm.	EPO; JPO;	
	į		DERWENT;	
			IBM_TDB	
•	1	(((ozonated or ozonating or ozonation or	USPAT;	2003/12/11
		ozonate)) near10 (film or layer) near10	US-PGPUB;	13:52
		oxide).clm. and nitride	EPO; JPO;	
			DERWENT;	
			IBM TDB	